SILICON PLASTIC POWER TRANSISTOR
PNP MJE2955T
10A 75W

Technical Data

…designed for general-purpose switching and amplifier application.

- ☞ DC Current Gain - h_{FE} = 20 – 100 @ IC = 4Adc
- ☞ Collector-Emitter Saturation Voltage – VCE(sat) = 1.1 Vdc (Max) @ IC = 4Adc
- ☞ Excellent Safe Operating Area
- ☞ TO-220 Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector- Emitter Voltage	V_{CEO}	60	Vdc
Collector – Base Voltage	V_{CB}	70	Vdc
Emitter Base Voltage	V_{EB}	5	Vdc
Collector Current – Continuos	I_C	10	Adc
Base Current – Continuos	I_B	6	Adc
Total Power Dissipation @ TC = 25°C Derate above 25°C	PD	75 0.6	Watts W/°C
Operating and Storage junction Temperature Range	Tj,Tstg	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Thermal resistance junction to case	R_{thjc}	1.67	°C/W

ISO 14001 CERTIFIED
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ELECTRICAL CHARACTERISTICS :[Tc = 25 °C unless otherwise noted]

Characteristic	Symbol	Min	Typ	Max	Unit
*** OFF CHARACTERISTICS :**					
Collector–Emitter Sustaining Voltage (1) [Ic =200 mAdc, I_B = 0]	$V_{CEO(sus)}$	60			Vdc
Collector Cutoff Current [V_{CB} = 70 Vdc, IE=0] [V_{CB}=70Vdc,I_E=0,T_C=150①C]	I_{CBO}			1.0	mAdc
Collector Cutoff Current [V_{CE} = 30 Vdc, I_B = 0]	I_{CE0}			0.70	mAdc
Collector Cutoff Current [V_{CE} = 70 Vdc, $V_{BE(off)}$ = 1.5 Vdc] [V_{CE}=70Vdc,$V_{BE(off)}$=1.5Vdc,T_C=150①C]	I_{CEX}			1.0	mAdc
Emitter Cutoff Current [V_{BE} = 5.0 Vdc , Ic = 0]	I_{EBO}			5.0	mAdc
*** ON CHARACTERISTICS (1):**					
DC Current Gain [Ic = 4.0 Adc , V_{CE} = 4.0 Vdc] [Ic = 10 Adc , V_{CE} = 4.0 Vdc]	h_{FE}	 20 5.0		 100	
Collector-Emitter Saturation Voltage [Ic = 4.0 Adc , I_B = 400 mAdc] [Ic = 10 Adc , I_B = 3.3 Adc]	$V_{CE(sat)}$			 1.1 8.0	Vdc
Base-Emitter on Voltage [Ic = 4.0 Adc , V_{CE}= 4.0. V_{DC}]	$V_{BE(on)}$			1.8	Vdc
SECOND BREAKDOWN					
Second Breakdown Collector current With Base Forward Biased [VCE=37.5Vdc, t = 1.0 s Nonrepetitive]	1s/b	2			Adc
DYNAMIC CHARACTERISTICS :					
Current Gain – Bandwidth Product [Ic = 0.5Adc , V_{CE}=10 Vdc , f=500kHz]	f_T	2.0			MHz

· (1) Pulse Test : Pulse Width <300μs , Duty Cycle < 2.0%